

In r application: Hwang et al.
Filed: 12/20/2001
Response Dated 06/24/2003

PAGE 2 OF 9

Serial No.: 10/029,008
Attorney's Docket: PAT021US
Reply to Office action f 04/09/2003

LISTING OF CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A monitored laser system, comprising:
 - a laser comprising
 - a first mirror,
 - an exit mirror, the first mirror having a reflectivity less than 100% but greater than that of the exit mirror,
 - at least a portion of a laser cavity defined by the first mirror and the exit mirror; and
 - an active region located in the laser cavity, the active region containing a material that is capable of stimulated emission at one or more wavelengths of laser light;
 - a multiple reflectivity band reflector (MRBR) ~~coupled to~~ positioned either (a) behind the first mirror or (b) to receive an output of an optical tap positioned to receive the laser light transmitted through the exit mirror, whereby the MRBR receives at least a portion of laser light emitted from the laser and transmittings filtered laser light, the MRBR having at least first and second wavelength bands with reflectivity above a particular reflectivity separated by at least a third wavelength band having reflectivity below the particular reflectivity;
 - a first photodiode coupled to at least a portion of the filtered laser light and producing an output based on the amount and wavelength of light received; and
 - means for adjusting the emitted wavelength of the laser toward a particular wavelength in one of the at least first, second, and third wavelength bands based at least in part on the output of the first photodiode.
2. (original) The monitored laser system of claim 1, wherein the particular wavelength is in the 1500-1600 nm range.
3. (original) The monitored laser system of claim 1, further comprising a power source coupled to the active region, wherein the means for adjusting the emitted wavelength includes a power source control.
4. (original) The monitored laser system of claim 1, wherein the means for adjusting the emitted wavelength includes a means for adjusting the temperature of the laser.
5. (original) The monitored laser system of claim 1, wherein the first mirror includes a plurality of layers and the means for adjusting the emitted wavelength modifies the refractive index of at least one of the layers.
6. (currently amended) The monitored laser system of claim 1, wherein the ~~portion of the laser light coupled to the MRBR is~~ positioned behind ~~transmitted through the first mirror.~~
7. (currently amended) The monitored laser system of claim 1, wherein the ~~portion of the~~

In re application: Hwang et al.
Filed: 12/20/2001
Response Dated 06/24/2003

PAGE 3 OF 9

Serial No.: 10/029,008
Attorney's Docket: PAT021US
Reply to Office action of 04/09/2003

laser light coupled to the MRBR is transmitted through the exit mirror positioned to receive an output of the optical tap.

8. (currently amended) The monitored laser system of claim 7, further comprising an optical tap having at least a first input and first and second outputs and wherein a portion of the laser light is coupled to the first input and the MRBR is coupled to the first output.

9. (original) The monitored laser system of claim 1, further comprising a second mirror and wherein the laser cavity is a two-section laser cavity defined by the first mirror, the exit mirror, and the second mirror.

10. (original) The monitored laser system of claim 1, further comprising a second photodiode coupled to at least a portion of the laser light and producing an output based on the amount and wavelength of light received; and wherein the means for adjusting the emitted wavelength of the laser toward a particular wavelength in one of the at least first, second, and third wavelength bands is based at least in part on both the output of the first photodiode and the output of the second photodiode.

11. (original) The monitored laser system of claim 1, wherein the MRBR has at least six wavelength bands with reflectivity above the particular reflectivity with at least one wavelength band with reflectivity below the particular reflectivity separating each sequential pair of the at least six wavelength bands.

12. (original) The monitored laser system of claim 11, wherein the six wavelength bands are within the range of 1500-1600 nm.

13. (original) The monitored laser system of claim 12, wherein the MRBR includes at least 60 material layers.

14. (original) The monitored laser system of claim 13, wherein the MRBR material layers include Al_2O_3 layers, TiO_2 layers, and SiO_2 layers.

15. The layer system of claim 14, wherein the MRBR material layers are based on the layer formula $\text{EABCD}(\text{ABC})^{60}\text{ABCD}(\text{ABC})^{60}\text{AB}$ with the layer identifiers corresponding to the following:

A representing Al_2O_3 , B representing TiO_2 , C representing SiO_2 , D representing Si, and E representing Al, with layers A-D having substantially the same thickness after adjustment for refractive index.

16. (original) The monitored laser system of claim 1, wherein the MRBR has at least thirteen wavelength bands with reflectivity above the particular reflectivity with at least one wavelength band with reflectivity below the particular reflectivity separating each sequential pair of the at least thirteen wavelength bands.

17. (original) The monitored laser system of claim 16, wherein the thirteen wavelength bands

In re application: Hwang et al.
Filed: 12/20/2001
Response Dated 06/24/2003

PAGE 4 OF 9

Serial No.: 10/029,008
Attorney's Docket: PAT021US
Reply to Office action of 04/09/2003

are within the range of 1500-1600 nm.

18. (original) The monitored laser system of claim 17, wherein the MRBR has layers based on the layer formula $ABC(ABCD)^2(ABDC)^{68}(ABCD)$ with the layer identifiers corresponding to the following:

A representing Al_2O_3 , B representing TiO_2 , C representing SiO_2 , and D representing Si, with layers A-C having substantially the same thickness after adjustment for refractive index and layer D having a thickness substantially 1/0.75 times that of layer A after adjustment for refractive index.

19. (original) The monitored laser system of claim 1, wherein the first and second wavelength bands include wavelengths specified in the ITU grid.

20. (original) The monitored laser system of claim 1, wherein the first reflectivity band includes a peak wavelength and the particular wavelength is equal to the peak wavelength.

21. (original) The monitored laser system of claim 1, wherein the third reflectivity band includes a trough wavelength and the particular wavelength is equal to the trough wavelength.

22. (currently amended) A method for monitoring a laser system comprising the steps of: pumping an active region located in a laser cavity of a laser, at least a portion of the laser cavity defined by a first mirror and an exit mirror, until laser light is emitted, the first mirror having a reflectivity less than 100% but greater than that of the exit mirror;

coupling positioning a multiple reflectivity band reflector (MRBR) to either (a) behind the first mirror or (b) to receive an output of an optical tap positioned to receive the laser light transmitted through the exit mirror, whereby the MRBR receives at least a portion of the emitted laser light and transmits filtered laser light, the MRBR having at least first and second wavelength bands with reflectivity above a particular reflectivity separated by at least a third wavelength band having reflectivity below the particular reflectivity, such that the MRBR transmits filtered laser light;

coupling at least a portion of the filtered laser light to a first photodiode such that an output is produced based on the amount and wavelength of light received by the first photodiode; and

adjusting the emitted wavelength of the laser toward a desired wavelength in one of the at least first, second, and third wavelength bands based at least in part on the output of the first photodiode.

23. (original) The method of claim 22, wherein the step of adjusting the emitted wavelength of the laser includes modifying the degree of pumping the active region.

24. (original) The method of claim 22, wherein the step of adjusting the emitted wavelength of the laser includes adjusting the temperature of the laser.

25. (original) The method of claim 22, wherein the first mirror includes a plurality of layers and the step of adjusting the emitted wavelength of the laser includes modifying the refractive index of at least one of the layers.

26. (original) The method of claim 22, further comprising the step of coupling at least a

In re application: Hwang et al.

PAGE 5 OF 9

Serial No.: 10/029,008

Filed: 12/20/2001

Attorney's Docket: PAT021US

Response Dated 06/24/2003

Reply to Office action of 04/09/2003

portion of the emitted laser light to a second photodiode such that an output is produced based on the amount and wavelength of light received by the second photodiode; and wherein the step of adjusting the emitted wavelength of the laser includes adjusting based at least in part on the output of both the first and second photodiodes.

27. (original) The method of claim 22, wherein the step of adjusting the emitted wavelength of the laser includes measuring an initial output of the first photodiode, modifying a tuning value by a positive step, measuring a new output of the first photodiode, and comparing the new output to the initial output.

28. (original) The method of claim 27, wherein the step of adjusting the emitted wavelength of the laser includes modifying the tuning value by a negative step.

29-32 (canceled)

33-38 (previously canceled)

39. (canceled)

40. (previously canceled)

41. (new) The method of claim 22, wherein the MRBR is positioned behind the first mirror.

42. (new) The method of claim 22, wherein the MRBR is positioned to receive an output of the optical tap.